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#### 4. Conclusion

In conclusion, we have shown that periodic arrays of Si nanopillars interact with incident electromagnetic radiation to produce Mie resonances that are consistent with dielectric nanocavities. This leads to the confinement of a large portion of the incident EM field within the subwavelength Si nanopillars as evidenced by FDTD and FEM simulations as well as  $\mu$ -Raman measurements. The resonances are observed to blue-shift linearly with decreasing nanopillar diameter, and less so with decreasing array pitch. The strong dependence of the resonance wavelength on the diameter of the Si nanopillars indicates that the local Mie resonance and the resonance-enhanced extinction in the high index Si nanopillars dominate the overall optical properties of the arrays. The pitch-induced shifts can be considered as the relatively weak, coherent coupling between these Si nanopillar Mie resonators, similar to effects studied widely for arrays of plasmonic particles. In addition, the dependence of these resonances on the nanoparticle and array parameters demonstrates that these resonances can be tuned to preferred wavelengths with specific linewidths and bandwidth for a given application. This can be useful in the development of photonic and plasmonic/photonic hybrid devices such as higher-efficiency photovoltaic solar cells and enhanced optical emitters and detectors.

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